

Features

- Uses advanced SGT technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)

Application

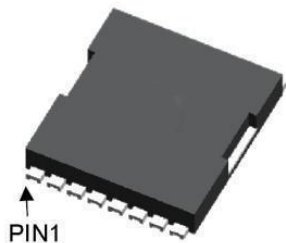
- Motor control and drive
- Battery management
- DC/DC

Product Summary

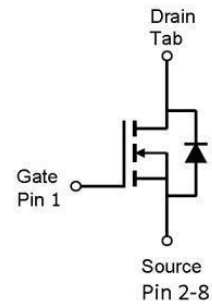
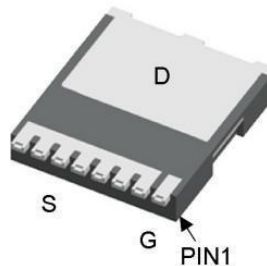
Package	TOLL
V_{DS}	40V
$R_{DS(on)}@V_{GS}=10V$	0.5mΩ
I_D	360A

Package Marking

TOLL Top View



TOLL Bottom View



Type	Package	Marking	Reel Size	Tape Width	Packing	Qty
LR006N04SD10	TOLL	LR006N04SD10	330*28.5mm	24mm	Reel&Tape	2000

Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous drain current $T_c=25^{\circ}C$ (Silicon limit) $T_A=25^{\circ}C$ (Package limit) $T_c=100^{\circ}C$ (Silicon limit)	I_D	603 360 379	A
Pulsed Drain Current	I_{DM}	2412	A
Maximum Power Dissipation	P_d	368	W
Single pulse avalanche energy	E_{AS}	2809	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Case	R_{thJC}	0.34	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	min	typ	max	Unit
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Static Characteristic

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	-	-	1	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 500	nA
Drain-source on-state resistance	$R_{DS(on)}$	$I_D=30A, V_{GS}=10V$	-	0.5	0.6	mΩ

Dynamic Characteristic

Input Capacitance	C_{iss}	$V_{DS}=20V, V_{GS}=0V,$ $f=1MHz$	-	16891	-	pF
Output Capacitance	C_{oss}		-	6480	-	
Reverse Transfer Capacitance	C_{rss}		-	1930	-	
Gate resistance	R_g	$f=1MHz$	-	1.09	-	Ω
Gate Total Charge	Q_g	$V_{DS}=20V, I_D=20A,$ $V_{GS}=10V$	-	224	-	nC
Gate-Source charge	Q_{gs}		-	82	-	
Gate-Drain charge	Q_{gd}		-	38	-	
Turn-on delay time	$t_{d(on)}$	$V_{GS}=10V, V_{DS}=20V,$ $R_G=3\Omega$	-	0.65	-	ns
Rise time	t_r		-	86	-	
Turn-off delay time	$t_{d(off)}$		-	98	-	
Fall time	t_f		-	57	-	

Body Diode Characteristic

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=30A$	-	0.7	1.2	v
Reverse Recovery Time	t_{rr}	$I_F=20A$ $di/dt=100A/\mu s$	-	113	-	ns
Reverse Recovery Charge	Q_{rr}		-	258	-	nC

Typical Performance Characteristics

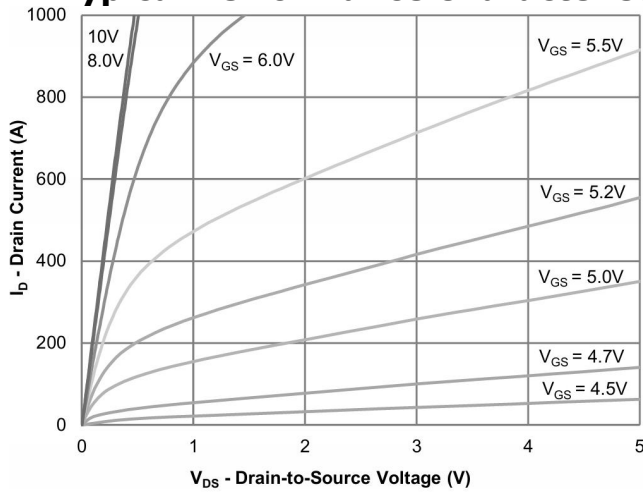


Figure 1: Output Characteristics

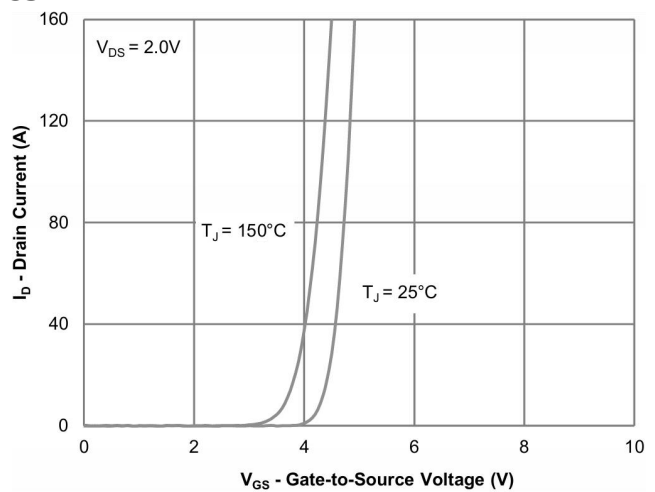


Figure 2: Transfer Characteristics

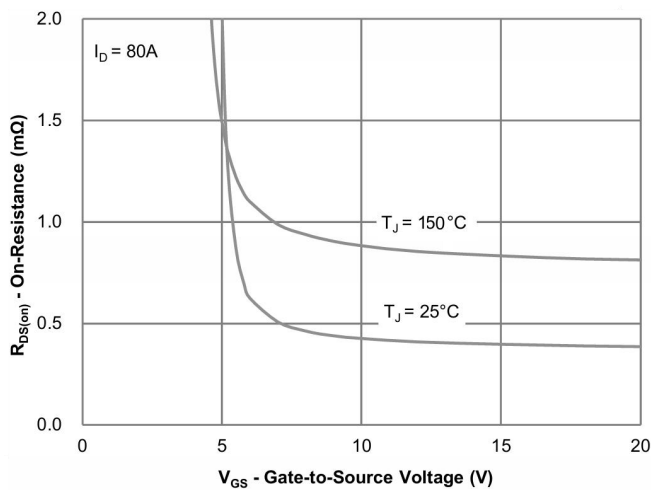


Figure 3: On-Resistance vs. Gate-Source Voltage

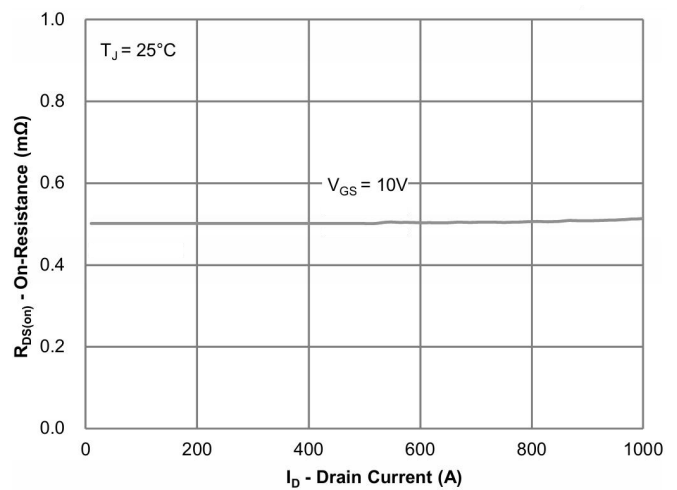


Figure 4: On-Resistance vs. Drain Current and Gate Voltage

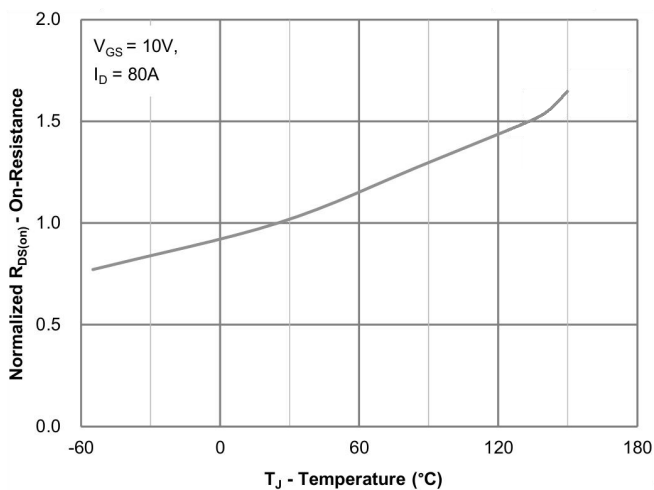


Figure 5: On-Resistance vs. Junction Temperature

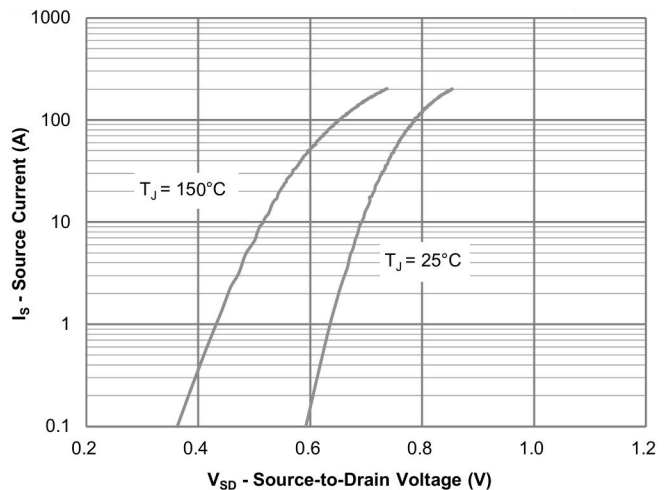


Figure 6: Source-Drain Diode Forward Voltage

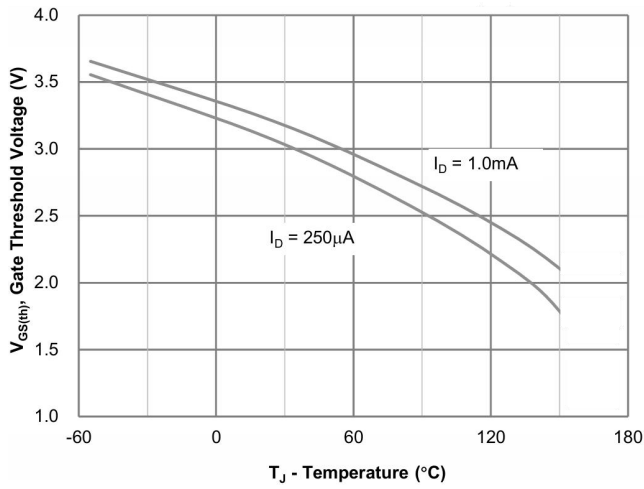


Figure 7: Gate Threshold Variation vs. Junction Temperature

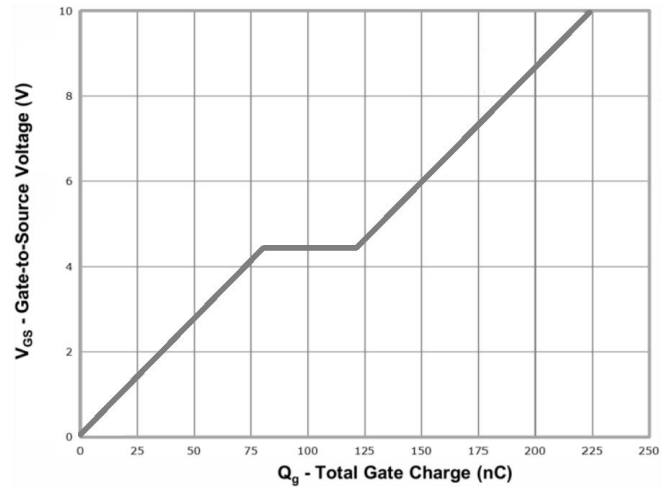


Figure 8: Gate Charge Characteristics

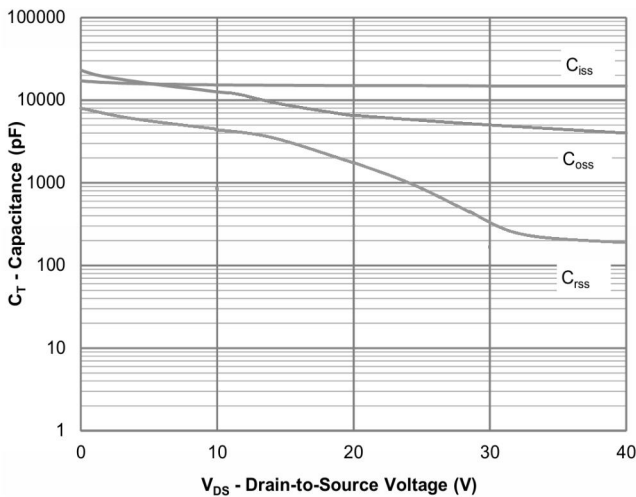


Figure 9: Capacitance Characteristics

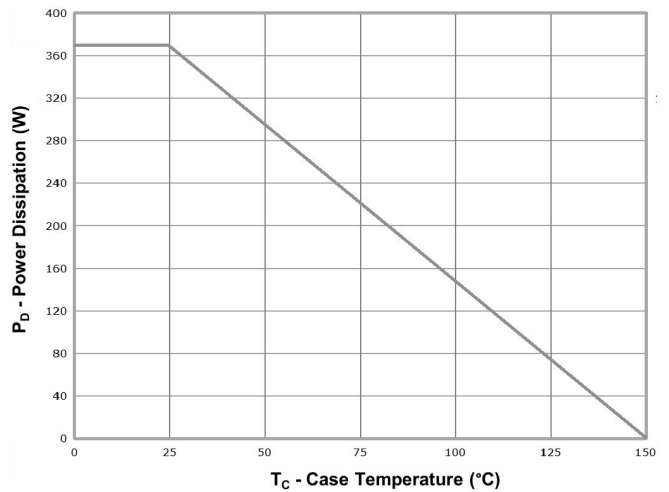


Figure 10: Power Derating

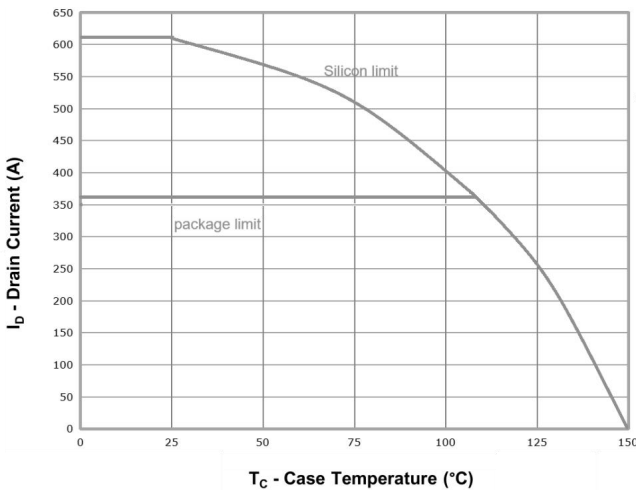


Figure 11: Current Derating

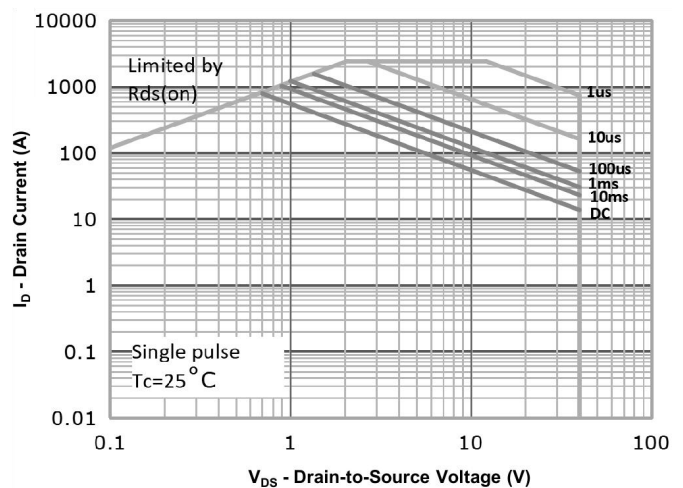


Figure 12: Safe Operating Area

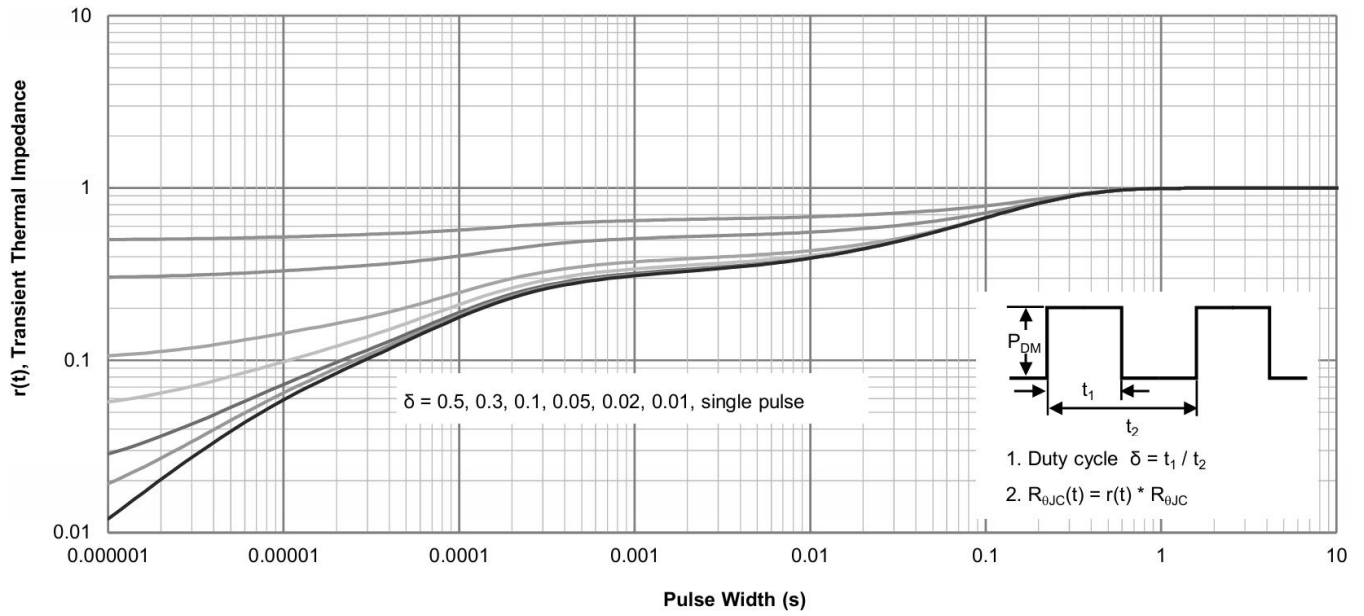
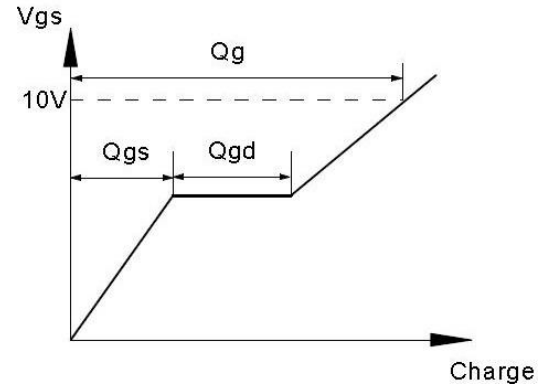
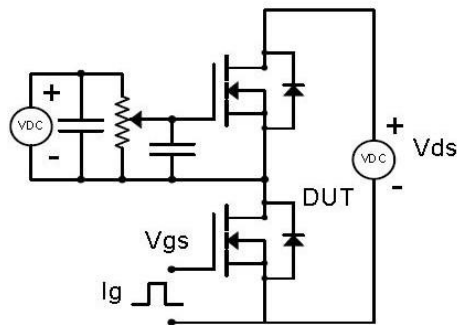


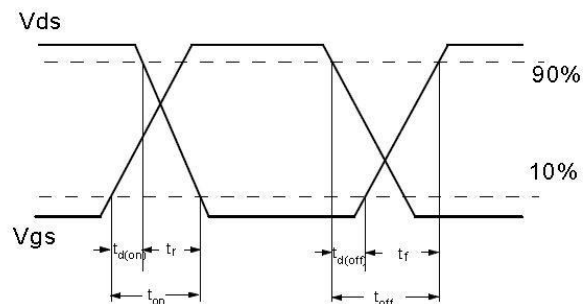
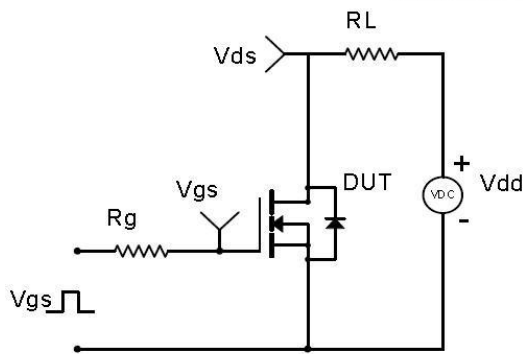
Figure 13: Normalized Maximum Transient Thermal Impedance

Test Circuit & Waveform

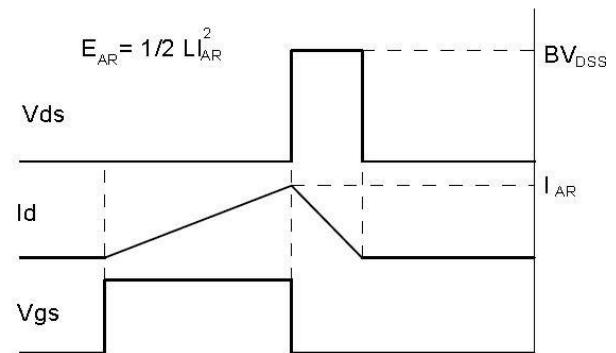
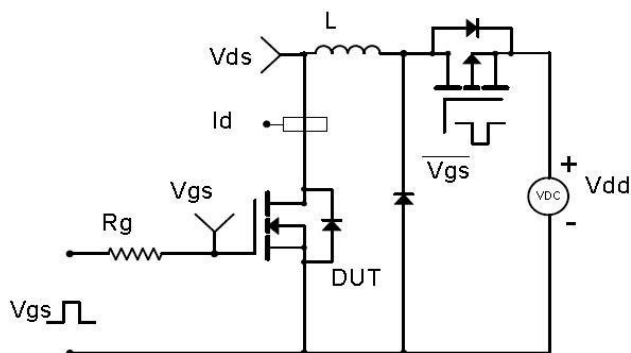
Gate Charge Test Circuit & Waveform



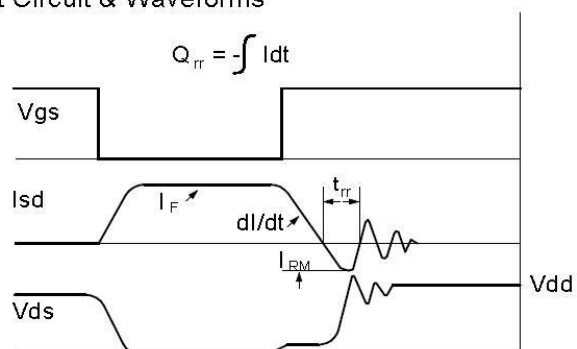
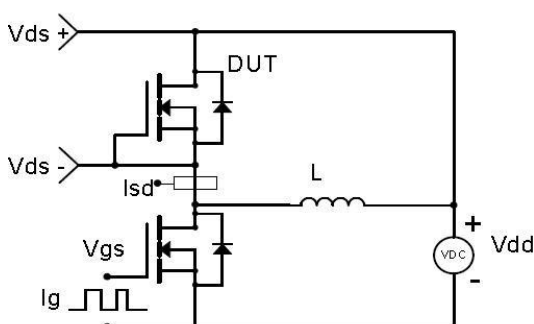
Resistive Switching Test Circuit & Waveforms



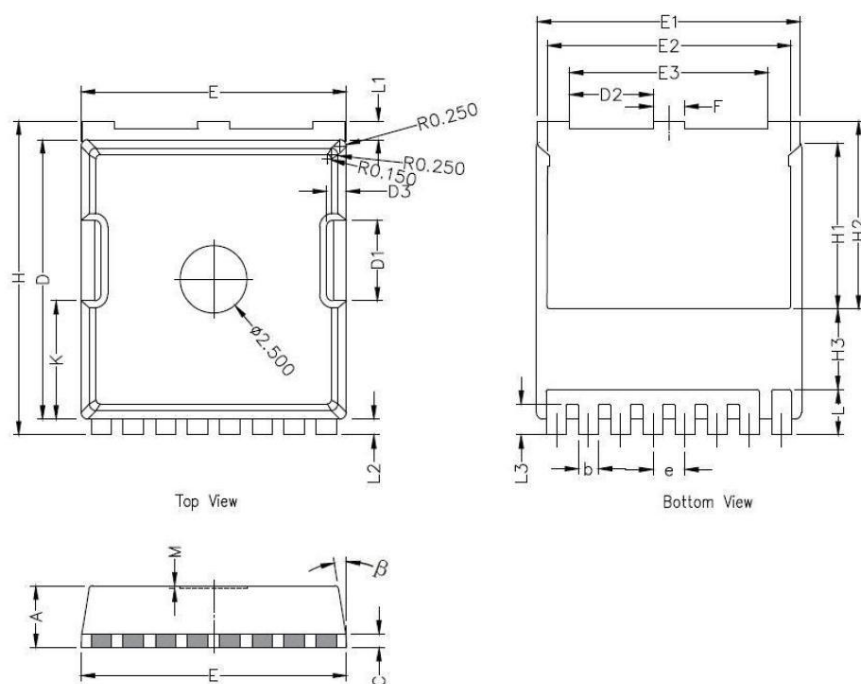
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline:TOLL



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
D2	2.95	3.10	3.25
D3	0.75 REF		
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.70	0.85
L2	0.45	0.60	0.75
L3	1.00	1.15	1.30
M	0.08 REF		
β	8°	10°	12°
K	4.25	4.40	4.55

Revision History:

Revision	Date	Major changes
1.0	2025/11/5	Release of Preliminary version.